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(71) Applicant: INTEL CORPORATION [US/US]; 2200 Mission College Boulevard, Santa Clara, CA 95054 (US).

(72) Inventors; and

(71) Applicants : KIM, Seiyon [KR/US]; 13062 Nw Corso Ln, Portland, OR 97229 (US). AUBERTINE, Daniel [US/US]; 11145 NW Timeric St., North Plains, OR 97133 (US). KUHN, Kelin [US/US]; 20280 SW Clarion St., Aloha, OR 97006 (US). MURTHY, Anand [US/US]; 10934 NW Lucerne Ct., Portland, OR 97229 (US).

(74) Agent: WINKLE, Robert; Winkle, PLLC., C/O Cpa Global, P.O. Box 52050, Minneapolis, MN 55402 (US).

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(54) Title: NANOWIRE TRANSISTOR WITH UNDERLAYER ETCH STOPS

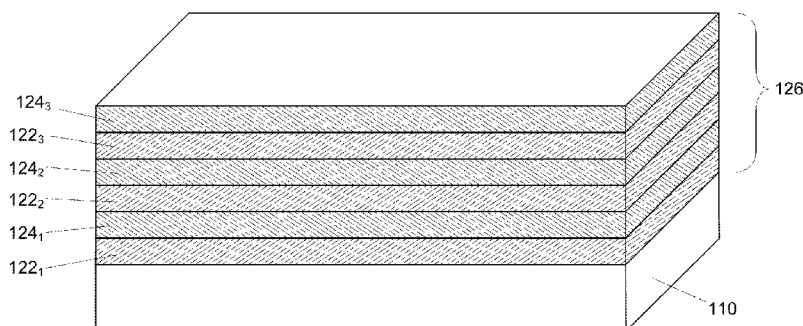


FIG. 1

(57) Abstract: A nanowire device of the present description may be produced with the incorporation of at least one underlayer etch stop formed during the fabrication of at least one nanowire transistor in order to assist in protecting source structures and/or drain structures from damage that may result from fabrication processes. The underlayer etch stop may prevent damage to the source structures and/or drain the structures, when the material used in the fabrication of the source structures and/or the drain structures is susceptible to being etched by the processes used in the removal of the sacrificial materials, i.e. low selectively to the source structure and/or the drain structure materials, such that potential shorting between the transistor gate electrodes and contacts formed for the source structures and/or the drain structures may be prevented.

